

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7	((selectivity selectively selective faster (higher near rate)) near3 etch\$3) near12 ((amorphous adj (Si silicon)) a-Si) near3 (SiGe GeSi ((germanium Ge) near1 (Silicon Si)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 13:15
L2	2	1 and ((ammonium adj hydroxide) or ((ammonia NH3 "NH.sub.3") near1 (aqueous solution)) or "NH.sub.4OH" "NH.sub.4 OH")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 13:18
L3	166472	((ammonium adj hydroxide) or ((ammonia NH3 "NH.sub.3") near1 (aqueous solution)) or "NH.sub.4OH" "NH.sub.4 OH")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 13:17
L4	2	1 and ((ammonium adj hydroxide) or ((ammonia NH3 "NH.sub.3") near1 (aqueous solution)) or "NH.sub.4OH" "NH.sub.4 OH")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 13:17
L5	0	1 near20 ((ammonium adj hydroxide) or ((ammonia NH3 "NH.sub.3") near1 (aqueous solution)) or "NH.sub.4OH" "NH.sub.4 OH")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 13:18
L6	0	1 same ((ammonium adj hydroxide) or ((ammonia NH3 "NH.sub.3") near1 (aqueous solution)) or "NH.sub.4OH" "NH.sub.4 OH")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 13:18
L7	0	1 same ((ammonium adj hydroxide) or ((ammonia NH3 "NH.sub.3") near1 (aqueous solution)) or "NH.sub.4OH" "NH.sub.4 OH")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 13:18
L8	0	1 near20 ((ammonium adj hydroxide) or ((ammonia NH3 "NH.sub.3") near1 (aqueous solution)) or "NH.sub.4OH" "NH.sub.4 OH")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 13:18
L10	0	1 and 3	USPAT	OR	OFF	2005/03/28 13:20

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	16062	(selectivity selectively selective) near3 etch\$3 near12 (amorphous adj silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 10:38
L2	228	((a-si) near3 (SiGe GeSi (Ge Germanium) near1 (Si Silicon)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 10:50
L3	8	1 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 10:48
L4	3	3 and (HF or hydrofluoric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 10:51
L5	599	("438/386").ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 10:49
L6	0	5 and ((a-si) near3 (SiGe GeSi (Ge Germanium) near1 (Si Silicon)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 10:49
L8	118	5 and ((a-si) or amorphous adj1 silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:24
L9	29	8 and (SiGe or GeSi or (Ge Germanium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:19

L10	11	9 and (HF or hydrofluoric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:19
L11	3446	((("438/243") or ("438/248") or ("438/249") or ("438/386") or ("438/391") or ("438/392") or ("438/3") or ("438/240"))).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:18
L12	1147	((("257/301"))).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:18
L14	4402	11 or 12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:19
L15	540	14 and (SiGe or GeSi or (Ge Germanium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:19
L16	210	15 and (HF or hydrofluoric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:19
L17	208	16 and (remove oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:19
L18	5	17 and ("NH.sub.4 OH")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:21

L19	72	17 and ((a-si)or amorphous adj1 silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:24
L20	69	19 not 18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:24
L21	60	20 not 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 11:24